ALPHA & OMEGA
SEMICONDUCTOR

AON6160

60V N-Channel AlphaSGT™

General Description

- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications
- RoHS and Halogen-Free Compliant

Product Summary

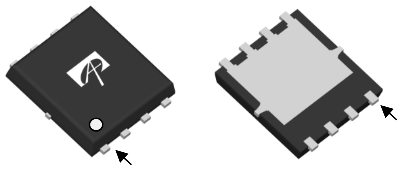
V_{DS}	60V
I_D (at V_{GS}=10V)	100A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 1.58mΩ

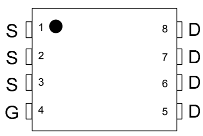
100% UIS Tested
100% Rg Tested

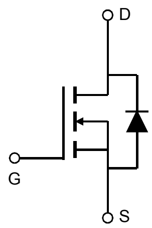
Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Industrial and Motor Drive applications

DFN5x6







Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON6160	DFN 5x6	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [G]	T_C=25°C	I_D	100	A
	T_C=100°C		100	
Pulsed Drain Current [C]		I_{DM}	400	
Continuous Drain Current	T_A=25°C	I_{DSM}	49	A
	T_A=70°C		39	
Avalanche Current [C]		I_{AS}	53	A
Avalanche energy	L=0.3mH [C]	E_{AS}	421	mJ
V_{DS} Spike	10µs	V_{SPIKE}	72	V
Power Dissipation [B]	T_C=25°C	P_D	215	W
	T_C=100°C		86	
Power Dissipation [A]	T_A=25°C	P_{DSM}	7.3	W
	T_A=70°C		4.7	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	14	17	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		40	50	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	0.43	0.58	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	60			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=$V_{GS,}$ I_D=250µA	2.1	2.55	3.4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		1.3	1.58	mΩ
		T_J=125°C		2.2	2.7	
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		90		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.66	1	V
I_S	Maximum Body-Diode Continuous Current [G]				100	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, f=1MHz	5180	6485	7790	pF
C_{oss}	Output Capacitance		730	1050	1370	pF
C_{rss}	Reverse Transfer Capacitance		5	30	55	pF
R_g	Gate resistance	f=1MHz	0.5	1.1	1.7	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=20A		85	120	nC
Q_{gs}	Gate Source Charge			24.5		nC
Q_{gd}	Gate Drain Charge			13		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=30V, R_L=1.5Ω, R_{GEN}=3Ω		19		ns
t_r	Turn-On Rise Time			10.5		ns
$t_{D(off)}$	Turn-Off DelayTime			51		ns
t_f	Turn-Off Fall Time			12		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs	15	33	50	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs	110	176	250	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

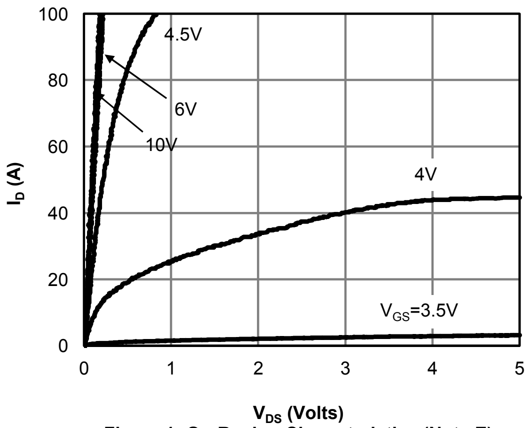


Figure 1: On-Region Characteristics (Note E)

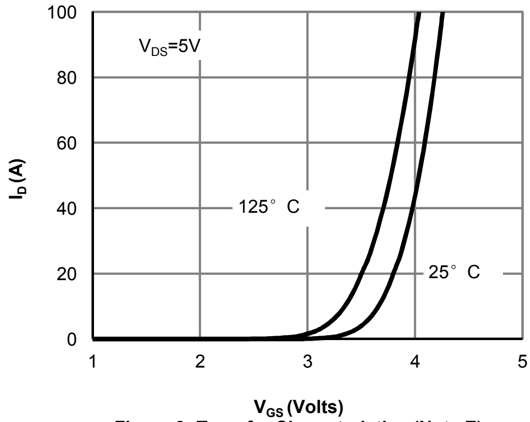


Figure 2: Transfer Characteristics (Note E)

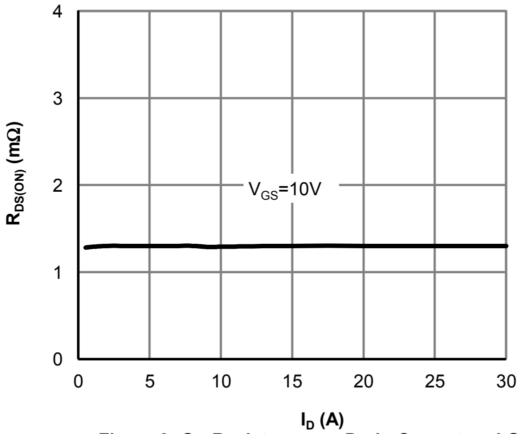


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

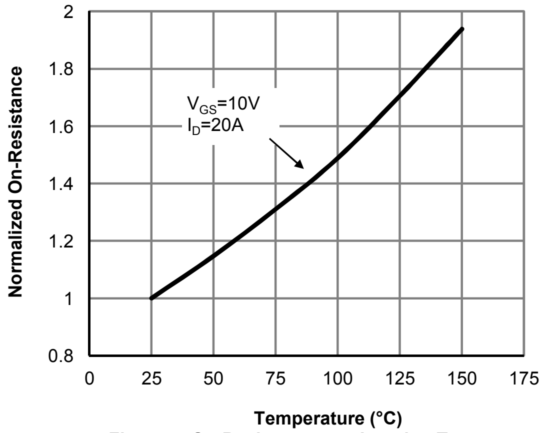


Figure 4: On-Resistance vs. Junction Temperature (Note E)

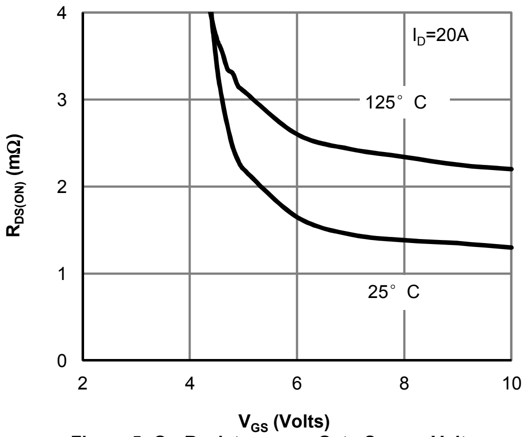


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

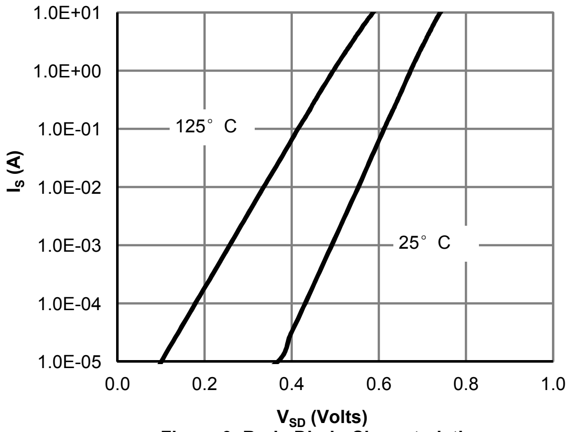


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

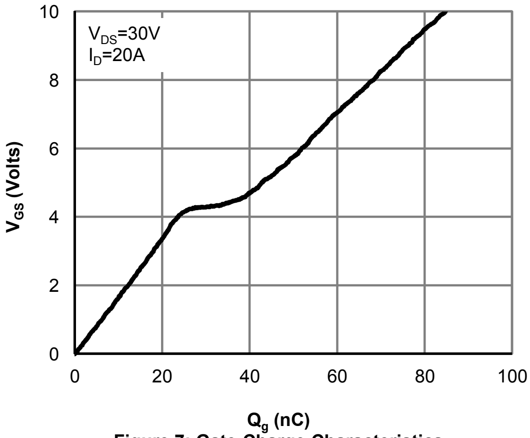


Figure 7: Gate-Charge Characteristics

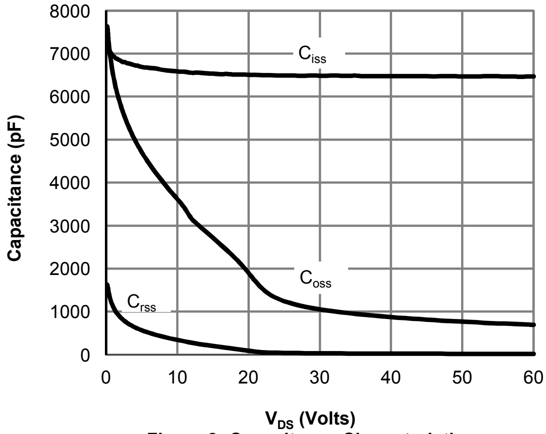
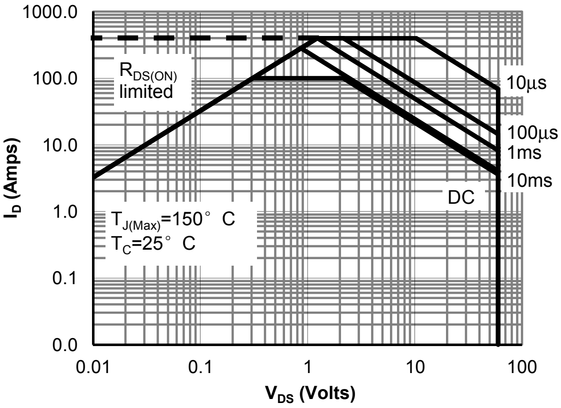


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 10V

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

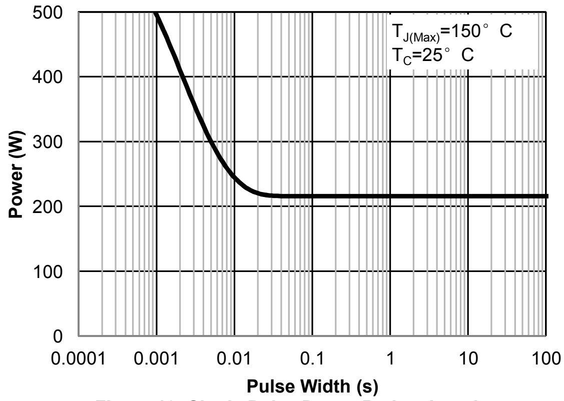


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

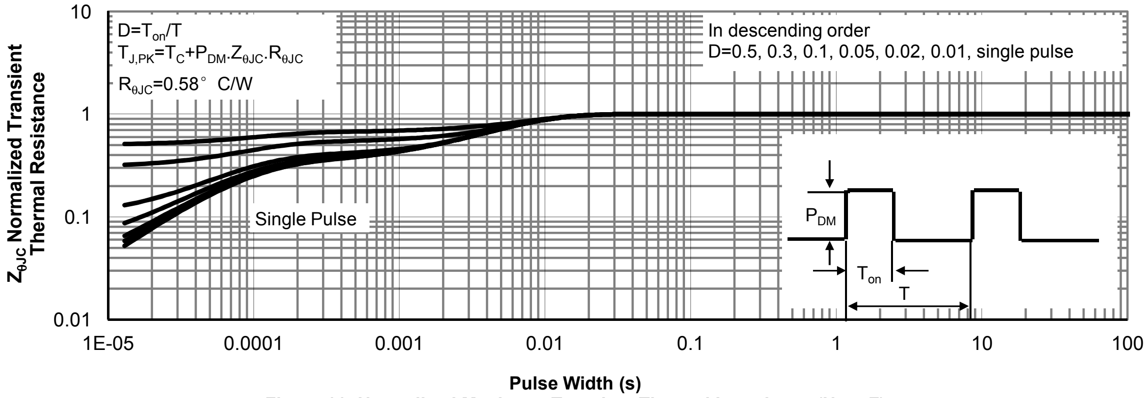


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

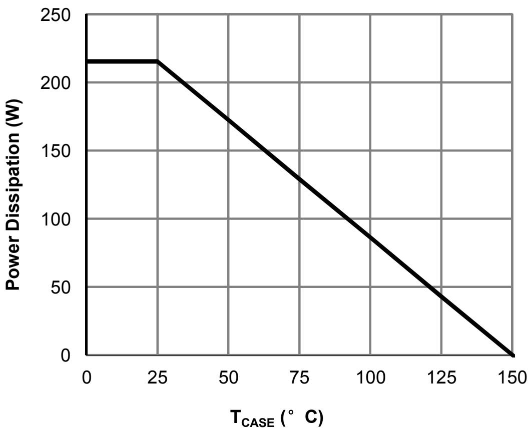


Figure 12: Power De-rating (Note F)

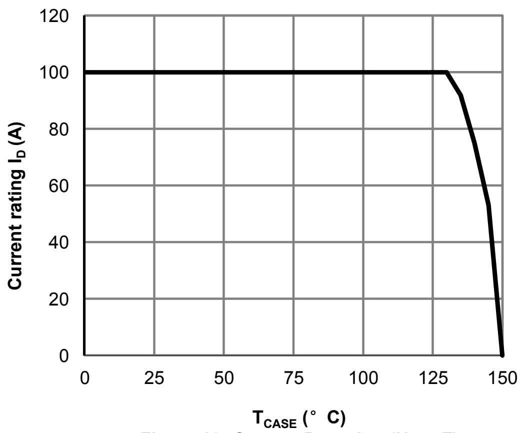


Figure 13: Current De-rating (Note F)

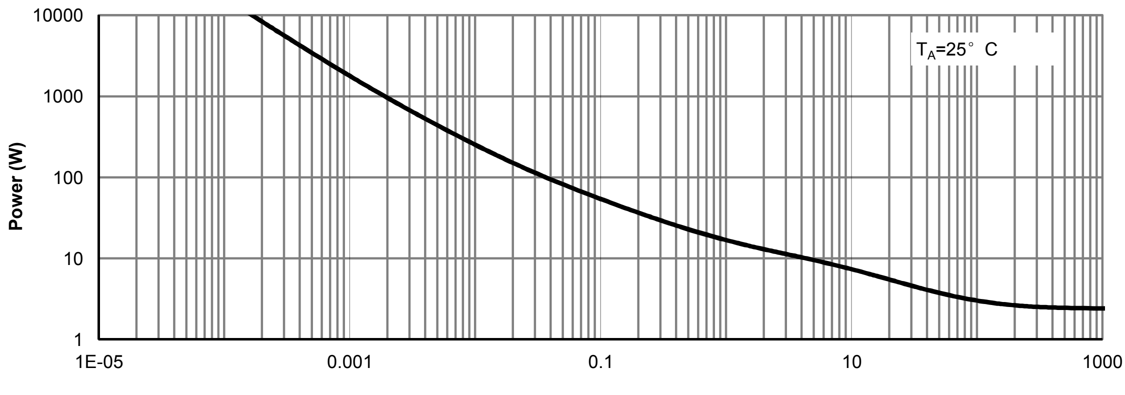


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

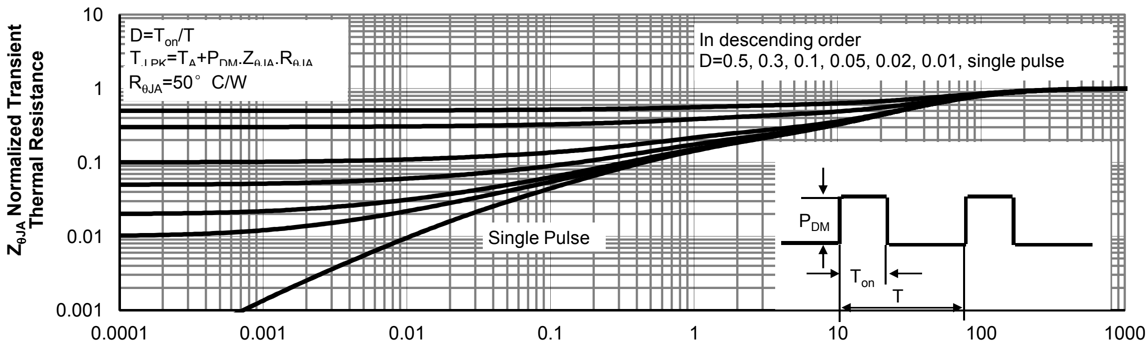


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

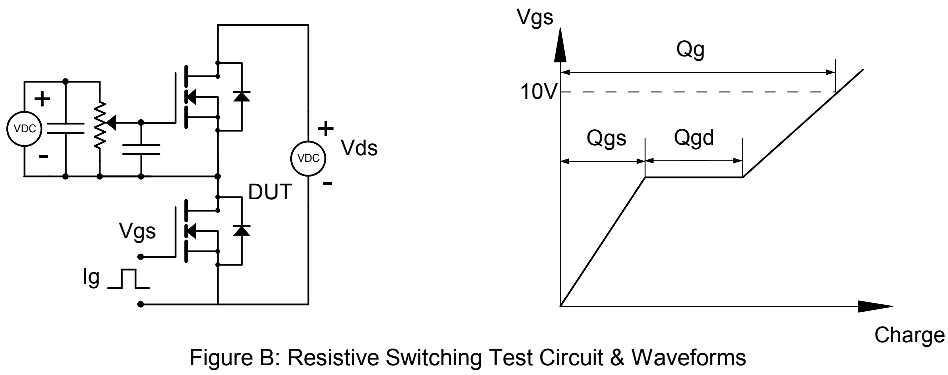


Figure B: Resistive Switching Test Circuit & Waveforms

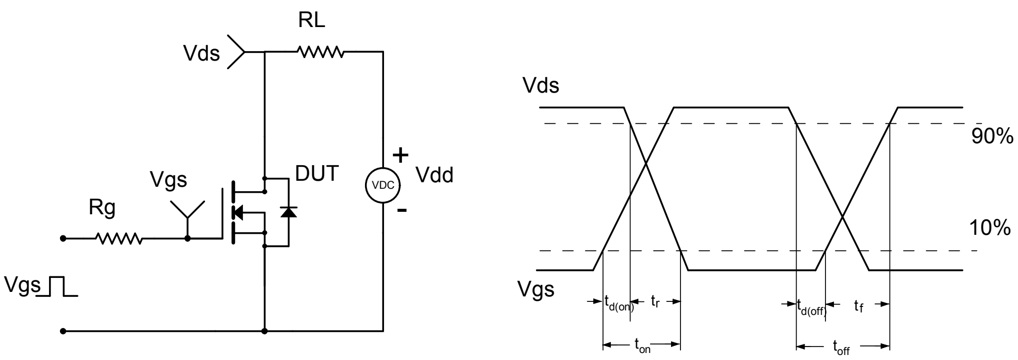


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

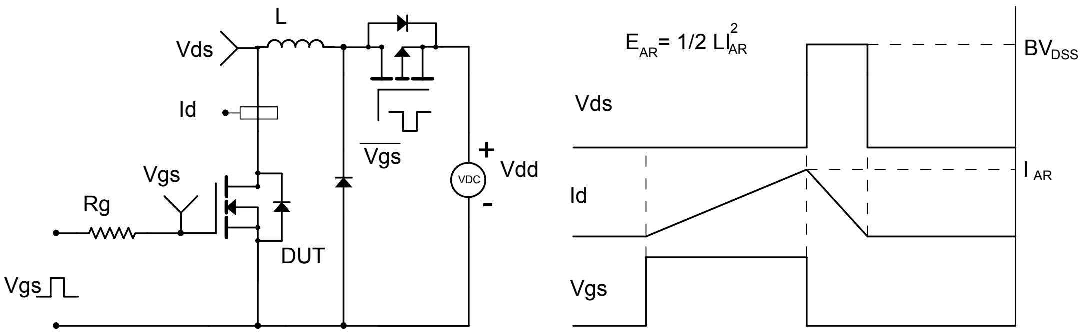


Figure D: Diode Recovery Test Circuit & Waveforms